



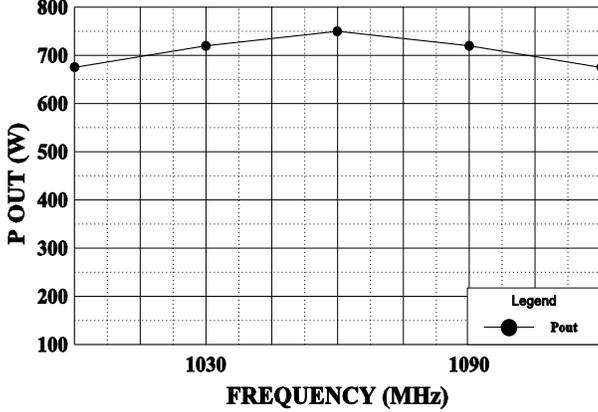
GHZ TECHNOLOGY
RF · MICROWAVE SILICON POWER TRANSISTORS

Typical Performance

TPR 700

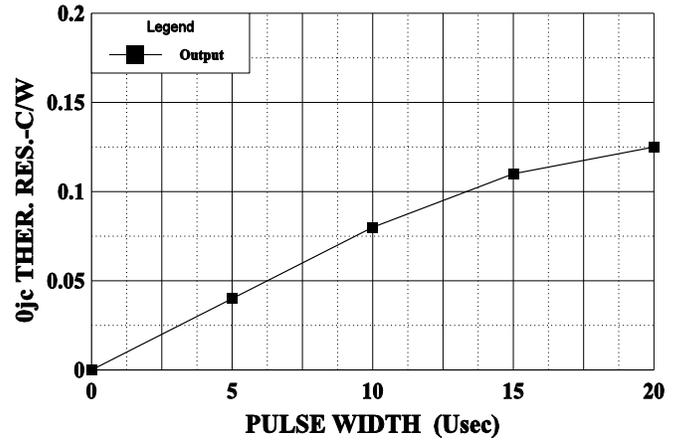
POWER OUTPUT VS FREQUENCY

Vcc = 50 V, Pin = 150 W, PW = 10us, 1%



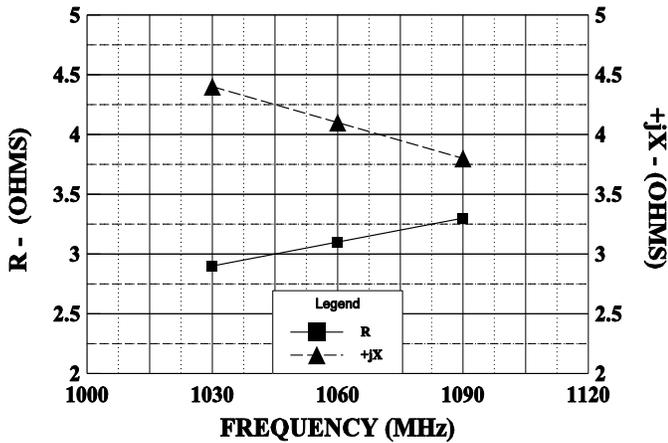
THERMAL RESISTANCE VS PULSE WIDTH

Vcc = 50 V, Tf = 30 C



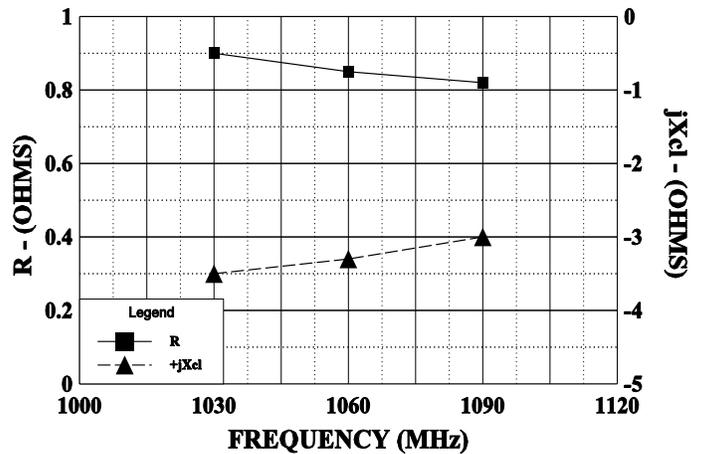
SERIES INPUT IMPEDANCE VS FREQUENCY

Vcc = 50 V, Pin = 150 W, PW = 10us, 1%



SERIES LOAD IMPEDANCE VS FREQUENCY

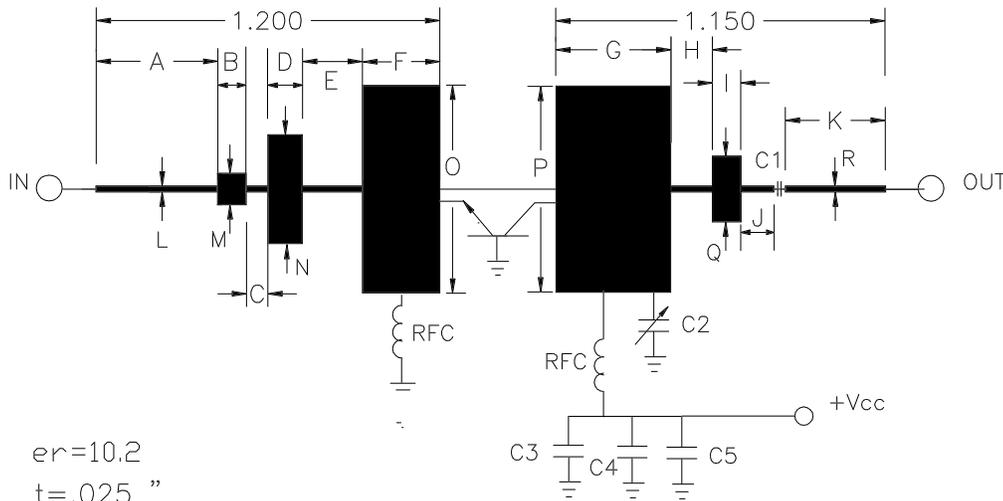
Vcc = 50 V, Po = 500 W, PW = 10us, 1%



REVISIONS

ZONE	REV	DESCRIPTION	DATE	APPROVED
------	-----	-------------	------	----------

DIM	INCHES
A	.425
B	.100
C	.075
D	.120
E	.210
F	.270
G	.400
H	.145
I	.100
J	.115
K	.350
L	.021
M	.110
N	.380
O	.725
P	.720
Q	.230
R	.021



$\epsilon_r = 10.2$
 $t = .025$ "
 C1, C3 = 100 pf Chip
 C2 = .3 - 3.5 pf
 C4 = 1 uf
 C5 = 220 uf

GHZ TPR 700
1030/1090 MHz

DATE: 5 OCT 95



CHz TECHNOLOGY

CAGE
OPJR2

DWG NO.

TPR 700

REV
1

SCALE

1.5/1

SHEET